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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	82
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l476vgt6tr

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Table 2. STM32L476xx family device features and peripheral counts (continued)

Peripheral	STM32L476 Zx	STM32L476 Qx	STM32L476 Vx	STM32L476 Mx	STM32L476 Jx	STM32L476 Rx
Max. CPU frequency	80 MHz					
Operating voltage	1.71 to 3.6 V					
Operating temperature	Ambient operating temperature: -40 to 85 °C / -40 to 105 °C / -40 to 125 °C Junction temperature: -40 to 105 °C / -40 to 125 °C / -40 to 130 °C					
Packages	LQFP144	UFBGA132	LQFP100	WLCSP81	WLCSP72	LQFP64

1. For the LQFP100 package, only FMC Bank1 is available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select.

Table 4. STM32L476 modes overview

Mode	Regulator (1)	CPU	Flash	SRAM	Clocks	DMA & Peripherals(2)	Wakeup source	Consumption(3)	Wakeup time
Run	Range 1	Yes	ON(4)	ON	Any	All	N/A	112 µA/MHz	N/A
	Range2					All except OTG_FS, RNG		100 µA/MHz	
LPRun	LPR	Yes	ON(4)	ON	Any except PLL	All except OTG_FS, RNG	N/A	136 µA/MHz	to Range 1: 4 µs to Range 2: 64 µs
Sleep	Range 1	No	ON(4)	ON(5)	Any	All	Any interrupt or event	37 µA/MHz	6 cycles
	Range 2					All except OTG_FS, RNG		35 µA/MHz	6 cycles
LPSleep	LPR	No	ON(4)	ON(5)	Any except PLL	All except OTG_FS, RNG	Any interrupt or event	40 µA/MHz	6 cycles
Stop 0	Range 1	No	Off	ON	LSE LSI	BOR, PVD, PVM RTC, LCD,IWDG COMPx (x=1,2) DACx (x=1,2) OPAMPx (x=1,2) USARTx (x=1...5)(6) LPUART1(6) I2Cx (x=1...3)(7) LPTIMx (x=1,2) *** All other peripherals are frozen.	Reset pin, all I/Os BOR, PVD, PVM RTC, LCD,IWDG COMPx (x=1..2) USARTx (x=1...5)(6) LPUART1(6) I2Cx (x=1...3)(7) LPTIMx (x=1,2) OTG_FS(8) SWPMI1(9)	108 µA	0.7 µs in SRAM 4.5 µs in Flash
	Range 2								

3.21 Liquid crystal display controller (LCD)

The LCD drives up to 8 common terminals and 44 segment terminals to drive up to 320 pixels.

- Internal step-up converter to guarantee functionality and contrast control irrespective of V_{DD}. This converter can be deactivated, in which case the VLCD pin is used to provide the voltage to the LCD
- Supports static, 1/2, 1/3, 1/4 and 1/8 duty
- Supports static, 1/2, 1/3 and 1/4 bias
- Phase inversion to reduce power consumption and EMI
- Integrated voltage output buffers for higher LCD driving capability
- Up to 8 pixels can be programmed to blink
- Unneeded segments and common pins can be used as general I/O pins
- LCD RAM can be updated at any time owing to a double-buffer
- The LCD controller can operate in Stop mode

3.22 Digital filter for Sigma-Delta Modulators (DFSDM)

The device embeds one DFSDM with 4 digital filters modules and 8 external input serial channels (transceivers) or alternately 8 internal parallel inputs support.

The DFSDM peripheral is dedicated to interface the external ΣΔ modulators to microcontroller and then to perform digital filtering of the received data streams (which represent analog value on ΣΔ modulators inputs). DFSDM can also interface PDM (Pulse Density Modulation) microphones and perform PDM to PCM conversion and filtering in hardware. DFSDM features optional parallel data stream inputs from microcontrollers memory (through DMA/CPU transfers into DFSDM).

DFSDM transceivers support several serial interface formats (to support various ΣΔ modulators). DFSDM digital filter modules perform digital processing according user selected filter parameters with up to 24-bit final ADC resolution.

Table 18. STM32L476xx memory map and peripheral register boundary addresses (continued)(1)

Bus	Boundary address	Size (bytes)	Peripheral
APB2	0x4001 6400 - 0x4001 FFFF	39 KB	Reserved
	0x4001 6000 - 0x4000 63FF	1 KB	DFSDM
	0x4001 5C00 - 0x4000 5FFF	1 KB	Reserved
	0x4001 5800 - 0x4000 5BFF	1 KB	SAI2
	0x4001 5400 - 0x4000 57FF	1 KB	SAI1
	0x4001 4C00 - 0x4000 53FF	2 KB	Reserved
	0x4001 4800 - 0x4001 4BFF	1 KB	TIM17
	0x4001 4400 - 0x4001 47FF	1 KB	TIM16
	0x4001 4000 - 0x4001 43FF	1 KB	TIM15
APB2	0x4001 3C00 - 0x4001 3FFF	1 KB	Reserved
	0x4001 3800 - 0x4001 3BFF	1 KB	USART1
	0x4001 3400 - 0x4001 37FF	1 KB	TIM8
	0x4001 3000 - 0x4001 33FF	1 KB	SPI1
	0x4001 2C00 - 0x4001 2FFF	1 KB	TIM1
	0x4001 2800 - 0x4001 2BFF	1 KB	SDMMC1
	0x4001 2000 - 0x4001 27FF	2 KB	Reserved
	0x4001 1C00 - 0x4001 1FFF	1 KB	FIREWALL
	0x4001 0800- 0x4001 1BFF	5 KB	Reserved
	0x4001 0400 - 0x4001 07FF	1 KB	EXTI
	0x4001 0200 - 0x4001 03FF	1 KB	COMP
	0x4001 0030 - 0x4001 01FF		VREFBUF
	0x4001 0000 - 0x4001 002F		SYSCFG

6.3.8 Internal clock source characteristics

The parameters given in *Table 47* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 22: General operating conditions*. The provided curves are characterization results, not tested in production.

High-speed internal (HSI16) RC oscillator

Table 47. HSI16 oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI16}	HSI16 Frequency	V_{DD}=3.0 V, T_A=30 °C	15.88	-	16.08	MHz
TRIM	HSI16 user trimming step	Trimming code is not a multiple of 64	0.2	0.3	0.4	%
		Trimming code is a multiple of 64	-4	-6	-8	
DuCy(HSI16)(2)	Duty Cycle	-	45	-	55	%
Δ_{Temp}(HSI16)	HSI16 oscillator frequency drift over temperature	T_A= 0 to 85 °C	-1	-	1	%
		T_A= -40 to 125 °C	-2	-	1.5	%
Δ_{VDD}(HSI16)	HSI16 oscillator frequency drift over V_{DD}	V_{DD}=1.62 V to 3.6 V	-0.1	-	0.05	%
t_{su}(HSI16)(2)	HSI16 oscillator start-up time	-	-	0.8	1.2	μs
t_{stab}(HSI16)(2)	HSI16 oscillator stabilization time	-	-	3	5	μs
I_{DD}(HSI16)(2)	HSI16 oscillator power consumption	-	-	155	190	μA

1. Guaranteed by characterization results.
2. Guaranteed by design.

6.3.10 Flash memory characteristics

Table 51. Flash memory characteristics(1)

Symbol	Parameter	Conditions	Typ	Max	Unit
t_{prog}	64-bit programming time	-	81.69	90.76	µs
t_{prog_row}	one row (32 double word) programming time	normal programming	2.61	2.90	ms
		fast programming	1.91	2.12	
t_{prog_page}	one page (2 Kbyte) programming time	normal programming	20.91	23.24	
		fast programming	15.29	16.98	
t_{ERASE}	Page (2 KB) erase time	-	22.02	24.47	
t_{prog_bank}	one bank (512 Kbyte) programming time	normal programming	5.35	5.95	s
		fast programming	3.91	4.35	
t_{ME}	Mass erase time (one or two banks)	-	22.13	24.59	ms
I_{DD}	Average consumption from V_{DD}	Write mode	3.4	-	mA
		Erase mode	3.4	-	
	Maximum current (peak)	Write mode	7 (for 2 µs)	-	
		Erase mode	7 (for 41 µs)	-	

1. Guaranteed by design.

Table 52. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min(1)	Unit
N_{END}	Endurance	T_A = –40 to +105 °C	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	15	
		1 kcycle(2) at T_A = 125 °C	7	
		10 kcycles(2) at T_A = 55 °C	30	
		10 kcycles(2) at T_A = 85 °C	15	
		10 kcycles(2) at T_A = 105 °C	10	

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

6.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 58* are derived from tests performed under the conditions summarized in *Table 22: General operating conditions*. All I/Os are designed as CMOS- and TTL-compliant (except BOOT0).

Table 58. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}(1)	I/O input low level voltage except BOOT0	1.62 V<V_{DDIOx}<3.6 V	-	-	0.3xV_{DDIOx} (2)	V
	I/O input low level voltage except BOOT0	1.62 V<V_{DDIOx}<3.6 V	-	-	0.39xV_{DDIOx}-0.06 (3)	
	I/O input low level voltage except BOOT0	1.08 V<V_{DDIOx}<1.62 V	-	-	0.43xV_{DDIOx}-0.1 (3)	
	BOOT0 I/O input low level voltage	1.62 V<V_{DDIOx}<3.6 V	-	-	0.17xV_{DDIOx} (3)	
V_{IH}(1)	I/O input high level voltage except BOOT0	1.62 V<V_{DDIOx}<3.6 V	0.7xV_{DDIOx} (2)	-	-	V
	I/O input high level voltage except BOOT0	1.62 V<V_{DDIOx}<3.6 V	0.49xV_{DDIOX}+0.26 (3)	-	-	
	I/O input high level voltage except BOOT0	1.08 V<V_{DDIOx}<1.62 V	0.61xV_{DDIOX}+0.05 (3)	-	-	
	BOOT0 I/O input high level voltage	1.62 V<V_{DDIOx}<3.6 V	0.77xV_{DDIOX} (3)	-	-	
V_{hys}(3)	TT_xx, FT_xxx and NRST I/O input hysteresis	1.62 V<V_{DDIOx}<3.6 V	-	200	-	mV
	FT_sx	1.08 V<V_{DDIOx}<1.62 V	-	150	-	
	BOOT0 I/O input hysteresis	1.62 V<V_{DDIOx}<3.6 V	-	200	-	

Equation 1: R_{AIN} max formula

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 64. Maximum ADC RAIN(1)(2)

Resolution	Sampling cycle @80 MHz	Sampling time [ns] @80 MHz	RAIN max (Ω)	
			Fast channels(3)	Slow channels(4)
12 bits	2.5	31.25	100	N/A
	6.5	81.25	330	100
	12.5	156.25	680	470
	24.5	306.25	1500	1200
	47.5	593.75	2200	1800
	92.5	1156.25	4700	3900
	247.5	3093.75	12000	10000
	640.5	8006.75	39000	33000
10 bits	2.5	31.25	120	N/A
	6.5	81.25	390	180
	12.5	156.25	820	560
	24.5	306.25	1500	1200
	47.5	593.75	2200	1800
	92.5	1156.25	5600	4700
	247.5	3093.75	12000	10000
	640.5	8006.75	47000	39000
8 bits	2.5	31.25	180	N/A
	6.5	81.25	470	270
	12.5	156.25	1000	680
	24.5	306.25	1800	1500
	47.5	593.75	2700	2200
	92.5	1156.25	6800	5600
	247.5	3093.75	15000	12000
	640.5	8006.75	50000	50000

Table 65. ADC accuracy - limited test conditions 1(1)(2)(3)

Symbol	Parameter	Conditions(4)			Min	Typ	Max	Unit
ET	Total unadjusted error	ADC clock frequency ≤ 80 MHz, Sampling rate ≤ 5.33 Msps, V_{DDA} = VREF+ = 3 V, TA = 25 °C	Single ended	Fast channel (max speed)	-	4	5	LSB
				Slow channel (max speed)	-	4	5	
			Differential	Fast channel (max speed)	-	3.5	4.5	
				Slow channel (max speed)	-	3.5	4.5	
EO	Offset error		Single ended	Fast channel (max speed)	-	1	2.5	
				Slow channel (max speed)	-	1	2.5	
			Differential	Fast channel (max speed)	-	1.5	2.5	
				Slow channel (max speed)	-	1.5	2.5	
EG	Gain error		Single ended	Fast channel (max speed)	-	2.5	4.5	
				Slow channel (max speed)	-	2.5	4.5	
			Differential	Fast channel (max speed)	-	2.5	3.5	
				Slow channel (max speed)	-	2.5	3.5	
ED	Differential linearity error		Single ended	Fast channel (max speed)	-	1	1.5	
				Slow channel (max speed)	-	1	1.5	
			Differential	Fast channel (max speed)	-	1	1.2	
				Slow channel (max speed)	-	1	1.2	
EL	Integral linearity error		Single ended	Fast channel (max speed)	-	1.5	2.5	
				Slow channel (max speed)	-	1.5	2.5	
			Differential	Fast channel (max speed)	-	1	2	
				Slow channel (max speed)	-	1	2	
ENOB	Effective number of bits		Single ended	Fast channel (max speed)	10.4	10.5	-	bits
				Slow channel (max speed)	10.4	10.5	-	
			Differential	Fast channel (max speed)	10.8	10.9	-	
				Slow channel (max speed)	10.8	10.9	-	
SINAD	Signal-to-noise and distortion ratio		Single ended	Fast channel (max speed)	64.4	65	-	dB
				Slow channel (max speed)	64.4	65	-	
			Differential	Fast channel (max speed)	66.8	67.4	-	
				Slow channel (max speed)	66.8	67.4	-	
SNR	Signal-to-noise ratio		Single ended	Fast channel (max speed)	65	66	-	
				Slow channel (max speed)	65	66	-	
			Differential	Fast channel (max speed)	67	68	-	
				Slow channel (max speed)	67	68	-	

Table 65. ADC accuracy - limited test conditions 1[(1)(2)(3)] (continued)

Sym-bol	Parameter	Conditions[(4)]			Min	Typ	Max	Unit
THD	Total harmonic distortion	ADC clock frequency ≤ 80 MHz, Sampling rate ≤ 5.33 Msps, $V_{DDA} = V_{REF+} = 3$ V, TA = 25 °C	Single ended	Fast channel (max speed)	-	-74	-73	dB
				Slow channel (max speed)	-	-74	-73	
			Differential	Fast channel (max speed)	-	-79	-76	
				Slow channel (max speed)	-	-79	-76	

1. Guaranteed by design.
2. ADC DC accuracy values are measured after internal calibration.
3. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
4. The I/O analog switch voltage booster is enable when $V_{DDA} < 2.4$ V (BOOSTEN = 1 in the SYSCFG_CFGR1 when $V_{DDA} < 2.4$ V). It is disable when $V_{DDA} \geq 2.4$ V. No oversampling.

Table 67. ADC accuracy - limited test conditions 3(1)(2)(3)

Sym-bol	Parameter	Conditions(4)			Min	Typ	Max	Unit
ET	Total unadjusted error	ADC clock frequency ≤ 80 MHz, Sampling rate ≤ 5.33 Msps, 1.65 V ≤ V_{DDA} = V_{REF+} ≤ 3.6 V, Voltage scaling Range 1	Single ended	Fast channel (max speed)	-	5.5	7.5	LSB
				Slow channel (max speed)	-	4.5	6.5	
			Differential	Fast channel (max speed)	-	4.5	7.5	
				Slow channel (max speed)	-	4.5	5.5	
EO	Offset error		Single ended	Fast channel (max speed)	-	2	5	
				Slow channel (max speed)	-	2.5	5	
			Differential	Fast channel (max speed)	-	2	3.5	
				Slow channel (max speed)	-	2.5	3	
EG	Gain error		Single ended	Fast channel (max speed)	-	4.5	7	
				Slow channel (max speed)	-	3.5	6	
			Differential	Fast channel (max speed)	-	3.5	4	
				Slow channel (max speed)	-	3.5	5	
ED	Differential linearity error		Single ended	Fast channel (max speed)	-	1.2	1.5	
				Slow channel (max speed)	-	1.2	1.5	
			Differential	Fast channel (max speed)	-	1	1.2	
				Slow channel (max speed)	-	1	1.2	
EL	Integral linearity error		Single ended	Fast channel (max speed)	-	3	3.5	
				Slow channel (max speed)	-	2.5	3.5	
			Differential	Fast channel (max speed)	-	2	2.5	
				Slow channel (max speed)	-	2	2.5	
ENOB	Effective number of bits		Single ended	Fast channel (max speed)	10	10.4	-	bits
				Slow channel (max speed)	10	10.4	-	
			Differential	Fast channel (max speed)	10.6	10.7	-	
				Slow channel (max speed)	10.6	10.7	-	
SINAD	Signal-to-noise and distortion ratio		Single ended	Fast channel (max speed)	62	64	-	dB
				Slow channel (max speed)	62	64	-	
			Differential	Fast channel (max speed)	65	66	-	
				Slow channel (max speed)	65	66	-	
SNR	Signal-to-noise ratio		Single ended	Fast channel (max speed)	63	65	-	
				Slow channel (max speed)	63	65	-	
			Differential	Fast channel (max speed)	66	67	-	
				Slow channel (max speed)	66	67	-	

6.3.20 Comparator characteristics

Table 72. COMP characteristics(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	-		1.62	-	3.6	V
V_{IN}	Comparator input voltage range	-		0	-	V_{DDA}	
V_{BG}(2)	Scaler input voltage	-		V_{REFINT}			
V_{SC}	Scaler offset voltage	-		-	±5	±10	mV
I_{DDA}(SCALER)	Scaler static consumption from V_{DDA}	BRG_EN=0 (bridge disable)		-	200	300	nA
		BRG_EN=1 (bridge enable)		-	0.8	1	µA
t_{START_SCALER}	Scaler startup time	-		-	100	200	µs
t_{START}	Comparator startup time to reach propagation delay specification	High-speed mode	$V_{DDA} \geq 2.7$ V	-	-	5	µs
			$V_{DDA} < 2.7$ V	-	-	7	
		Medium mode	$V_{DDA} \geq 2.7$ V	-	-	15	
			$V_{DDA} < 2.7$ V	-	-	25	
		Ultra-low-power mode		-	-	80	
t_D(3)	Propagation delay for 200 mV step with 100 mV overdrive	High-speed mode	$V_{DDA} \geq 2.7$ V	-	55	80	ns
			$V_{DDA} < 2.7$ V	-	65	100	
		Medium mode	$V_{DDA} \geq 2.7$ V	-	0.55	0.9	µs
			$V_{DDA} < 2.7$ V	-	0.65	1	
		Ultra-low-power mode		-	5	12	
V_{offset}	Comparator offset error	Full common mode range	-	-	±5	±20	mV
V_{hys}	Comparator hysteresis	No hysteresis		-	0	-	mV
		Low hysteresis		-	8	-	
		Medium hysteresis		-	15	-	
		High hysteresis		-	27	-	
I_{DDA}(COMP)	Comparator consumption from V_{DDA}	Ultra-low-power mode	Static	-	400	600	nA
			With 50 kHz ±100 mV overdrive square signal	-	1200	-	
		Medium mode	Static	-	5	7	µA
			With 50 kHz ±100 mV overdrive square signal	-	6	-	
		High-speed mode	Static	-	70	100	
			With 50 kHz ±100 mV overdrive square signal	-	75	-	

Table 73. OPAMP characteristics(1) (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{network}$	R2/R1 internal resistance values in PGA mode(5)	PGA Gain = 2		-	80/80	-	kΩ/kΩ
		PGA Gain = 4		-	120/ 40	-	
		PGA Gain = 8		-	140/ 20	-	
		PGA Gain = 16		-	150/ 10	-	
Delta R	Resistance variation (R1 or R2)	-		-15	-	15	%
PGA gain error	PGA gain error	-		-1	-	1	%
PGA BW	PGA bandwidth for different non inverting gain	Gain = 2	-	-	GBW/ 2	-	MHz
		Gain = 4	-	-	GBW/ 4	-	
		Gain = 8	-	-	GBW/ 8	-	
		Gain = 16	-	-	GBW/ 16	-	
en	Voltage noise density	Normal mode	at 1 kHz, Output loaded with 4 kΩ	-	500	-	nV/√Hz
		Low-power mode	at 1 kHz, Output loaded with 20 kΩ	-	600	-	
		Normal mode	at 10 kHz, Output loaded with 4 kΩ	-	180	-	
		Low-power mode	at 10 kHz, Output loaded with 20 kΩ	-	290	-	
I_{DDA}(OPAMP)(3)	OPAMP consumption from V_{DDA}	Normal mode	no Load, quiescent mode	-	120	260	µA
		Low-power mode		-	45	100	

1. Guaranteed by design, unless otherwise specified.
2. The temperature range is limited to 0 °C-125 °C when V_{DDA} is below 2 V
3. Guaranteed by characterization results.
4. Mostly I/O leakage, when used in analog mode. Refer to I_{lkg} parameter in *Table 58: I/O static characteristics*.
5. R2 is the internal resistance between OPAMP output and OPAMP inverting input. R1 is the internal resistance between OPAMP inverting input and ground. The PGA gain =1+R2/R1

SAI characteristics

Unless otherwise specified, the parameters given in *Table 86* for SAI are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 22: General operating conditions*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 x V_{DD}

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (CK,SD,FS).

Table 86. SAI characteristics[1]

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCLK}	SAI Main clock output	-	-	50	MHz
f_{CK}	SAI clock frequency[2]	Master transmitter $2.7 \leq V_{DD} \leq 3.6$ Voltage Range 1	-	18.5	MHz
		Master transmitter $1.71 \leq V_{DD} \leq 3.6$ Voltage Range 1	-	12.5	
		Master receiver Voltage Range 1	-	25	
		Slave transmitter $2.7 \leq V_{DD} \leq 3.6$ Voltage Range 1	-	22.5	
		Slave transmitter $1.71 \leq V_{DD} \leq 3.6$ Voltage Range 1	-	14.5	
		Slave receiver Voltage Range 1	-	25	
		Voltage Range 2	-	12.5	
$t_{v(FS)}$	FS valid time	Master mode $2.7 \leq V_{DD} \leq 3.6$	-	22	ns
		Master mode $1.71 \leq V_{DD} \leq 3.6$	-	40	
$t_{h(FS)}$	FS hold time	Master mode	10	-	ns
$t_{su(FS)}$	FS setup time	Slave mode	1	-	ns
$t_{h(FS)}$	FS hold time	Slave mode	2	-	ns
$t_{su(SD\_A\_MR)}$	Data input setup time	Master receiver	2.5	-	ns
$t_{su(SD\_B\_SR)}$		Slave receiver	3	-	
$t_{h(SD\_A\_MR)}$	Data input hold time	Master receiver	8	-	ns
$t_{h(SD\_B\_SR)}$		Slave receiver	4	-	

Table 93. Asynchronous non-multiplexed SRAM/PSRAM/NOR write-NWAIT timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}+0.5$	$8T_{HCLK}+0.5$	ns
$t_{w(NWE)}$	FMC_NWE low time	$6T_{HCLK}-0.5$	$6T_{HCLK}+0.5$	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$6T_{HCLK}+2$	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+2$	-	

1. CL = 30 pF.
2. Guaranteed by characterization results.

Figure 39. Asynchronous multiplexed PSRAM/NOR read waveforms

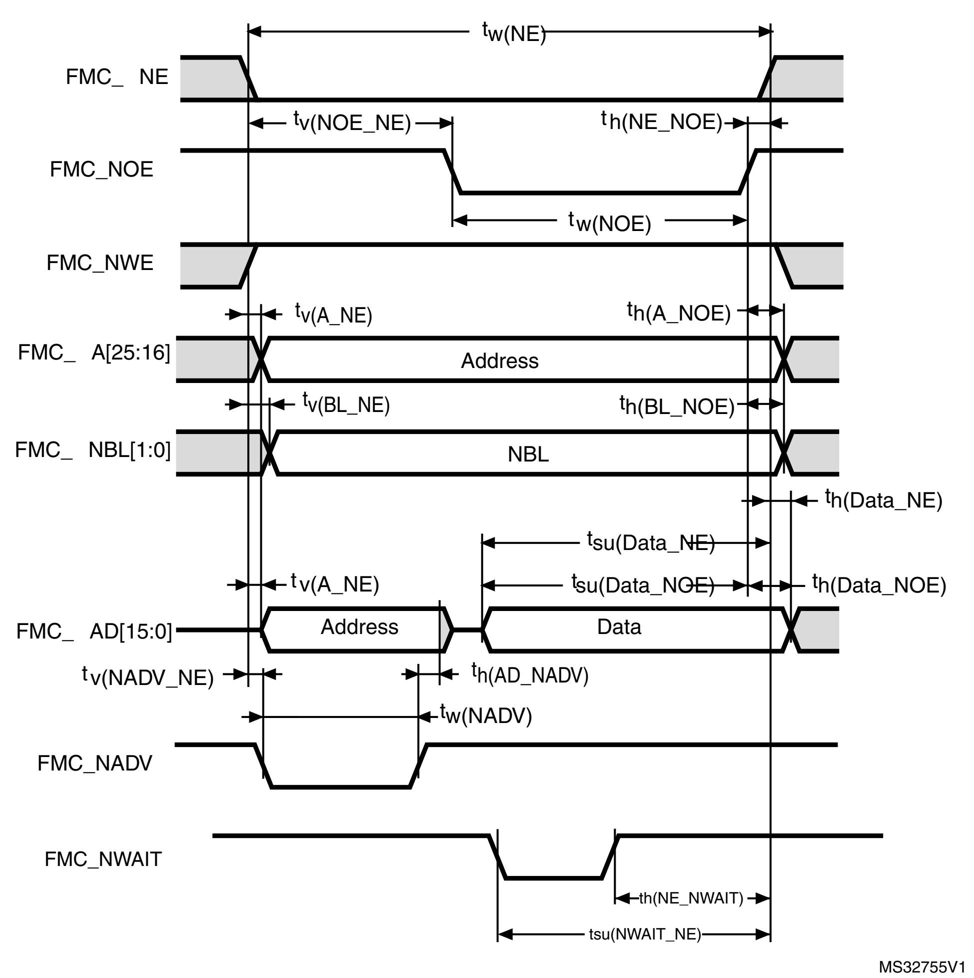


Figure 45. NAND controller waveforms for read access

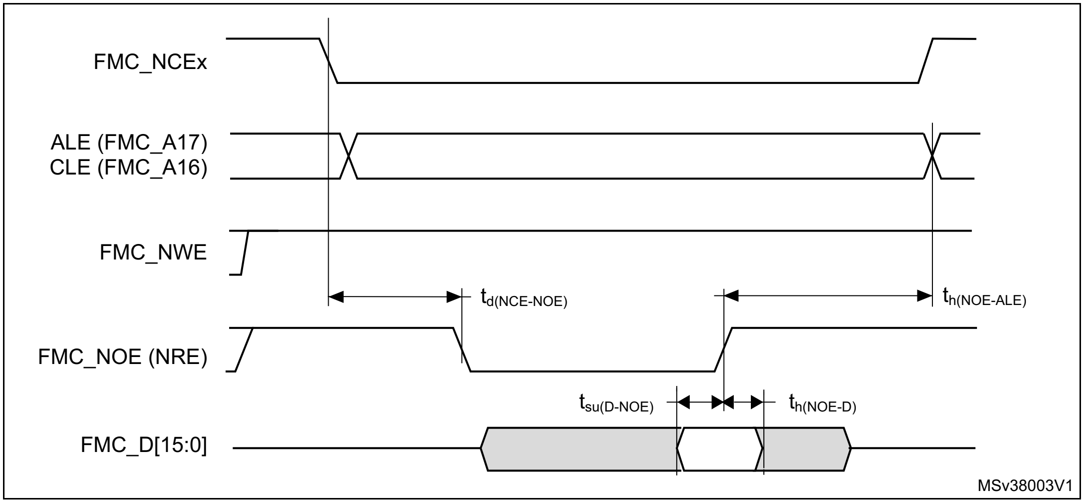


Figure 46. NAND controller waveforms for write access

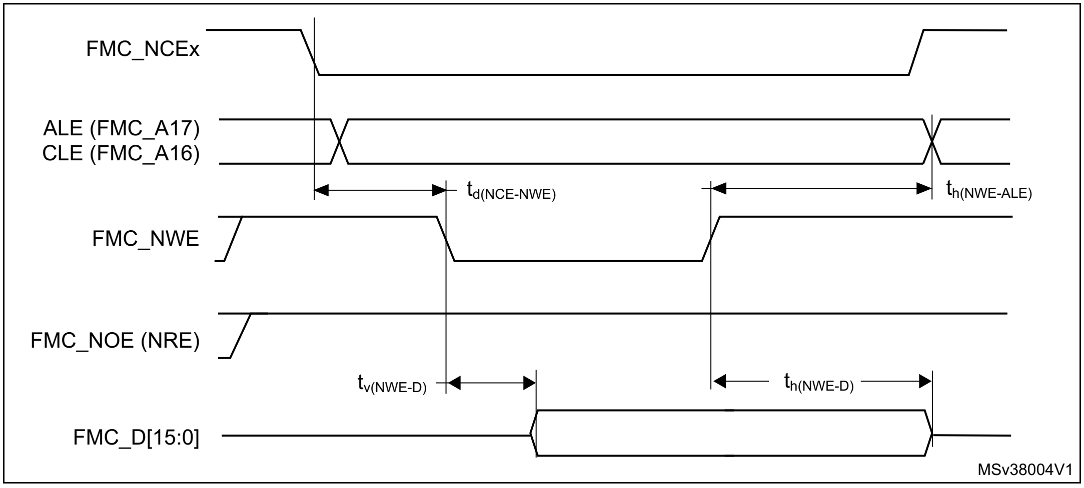


Figure 47. NAND controller waveforms for common memory read access

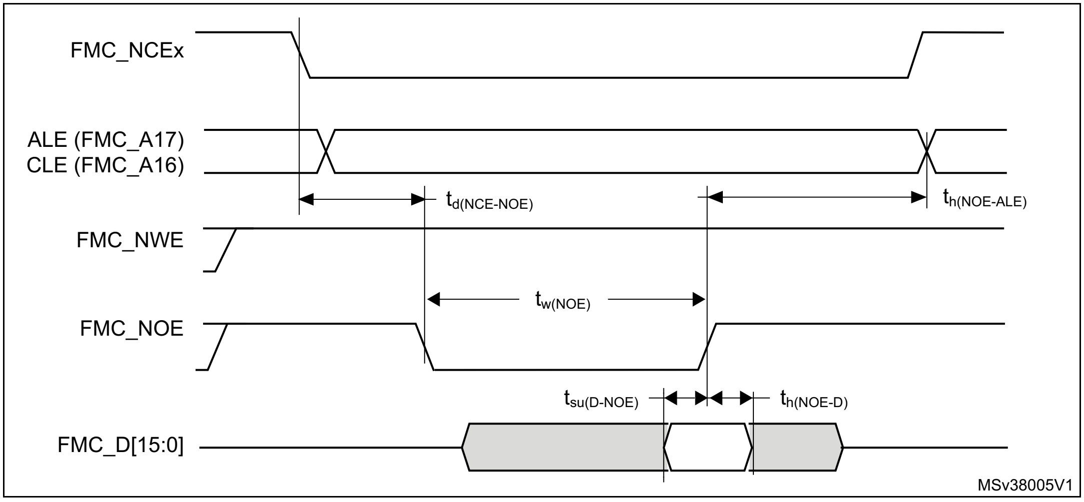
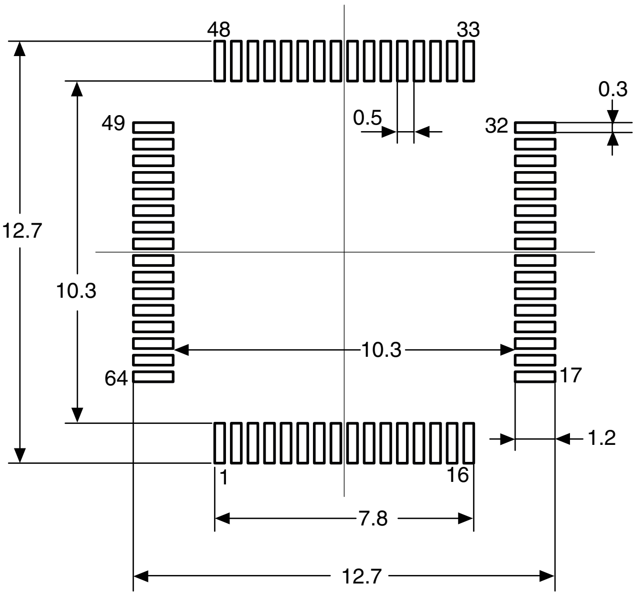


Table 112. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
E3	-	7.500	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 65. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

7.7 Thermal characteristics

The maximum chip junction temperature ($T_J$max) must never exceed the values given in *Table 22: General operating conditions*.

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max x } \Theta_{JA})$$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DDIOx} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 113. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** LQFP64 - 10 × 10 mm / 0.5 mm pitch	45	°C/W
	Thermal resistance junction-ambient LQFP100 - 14 × 14mm	42	
	Thermal resistance junction-ambient LQFP144 - 20 × 20 mm	32	
	Thermal resistance junction-ambient UFBGA132 - 7 × 7 mm	55	
	Thermal resistance junction-ambient WLCSP72	46	
	Thermal resistance junction-ambient WLCSP81	41	

7.7.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org

7.7.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Section 8: Part numbering*.

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

9 Revision history

Table 115. Document revision history

Date	Revision	Changes
29-May-2015	1	Initial release.
15-Jun-2015	2	Updated *Table 1: Device summary* and *Table 72: COMP characteristics*.
18-Sep-2015	3	Changed alternate function pin name “SWDAT” into “SWDIO” in all the document. Updated *Section 3.9.1: Power supply schemes*. Updated *Section 3.15.1: Temperature sensor*. In all *Section 6: Electrical characteristics*, renamed table footnotes related to test and characterization. Added *Note 2*. Updated *Table 41: Low-power mode wakeup timings*. Updated *Table 42: Regulator modes transition times*. Updated *Table 47: HSI16 oscillator characteristics*. Added *Table 20: HSI16 frequency versus temperature*. Updated *Table 48: MSI oscillator characteristics*. Updated *Table 49: LSI oscillator characteristics*. Updated *Table 57: I/O current injection susceptibility*. Removed first Note in *Table 58: I/O static characteristics*. Removed second Note in *Table 59: Output voltage characteristics*. Updated *Table 63: ADC characteristics*. Updated *Table 65: ADC accuracy - limited test conditions 1*. Added *Table 66: ADC accuracy - limited test conditions 2*. Added *Table 67: ADC accuracy - limited test conditions 3*. Added *Table 68: ADC accuracy - limited test conditions 4*. Updated *Table 70: DAC accuracy*. Updated *Table 71: VREFBUF characteristics*. Added *Section 6.3.25: DFSDM characteristics*. Updated *Section : Quad SPI characteristics*. Updated *Table 84: Quad SPI characteristics in SDR mode*. Updated *Table 85: QUADSPI characteristics in DDR mode*. Updated *Table 89: USB electrical characteristics*. Updated *Section 7.2: UFBGA132 package information*. Updated *Section 7.5: WLCSP72 package information*. Updated *Table 66: LQFP64 marking (package top view)*.